## **74AUP1T34**

# **Low-power dual supply translating buffer** Rev. 5 — 4 September 2013

**Product data sheet** 

#### **General description** 1.

The 74AUP1T34 provides a single buffer with two separate supply voltages. Input A is designed to track  $V_{CC(A)}$ . Output Y is designed to track  $V_{CC(Y)}$ . Both,  $V_{CC(A)}$  and  $V_{CC(Y)}$ accepts any supply voltage from 1.1 V to 3.6 V. This feature allows universal low voltage interfacing between any of the 1.2 V, 1.5 V, 1.8 V, 2.5 V, and 3.3 V voltage nodes.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V<sub>CC</sub> range from 1.1 V to 3.6 V. This device ensures a very low static and dynamic power consumption across the entire V<sub>CC</sub> range from 1.1 V to 3.6 V. This device is fully specified for partial power-down applications using I<sub>OFF</sub>.

The I<sub>OFF</sub> circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

#### Features and benefits 2.

- Wide supply voltage range from 1.1 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
  - ◆ JESD8-7 (1.2 V to 1.95 V)
  - ◆ JESD8-5 (1.8 V to 2.7 V)
  - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - HBM JESD22-A114F Class 3A exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 1000 V
- Wide supply voltage range:
  - ◆ V<sub>CC(A)</sub>: 1.1 V to 3.6 V
  - V<sub>CC(Y)</sub>: 1.1 V to 3.6 V
- Low static power consumption;  $I_{CC} = 0.9 \mu A$  (maximum)
- Each port operates over the full 1.1 V to 3.6 V power supply range
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- I<sub>OFF</sub> circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



#### Low-power dual supply translating buffer

### 3. Ordering information

Table 1. Ordering information

Type number	Package								
	Temperature range	Name	Description	Version					
74AUP1T34GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1					
74AUP1T34GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1.45 $\times$ 0.5 mm	SOT886					
74AUP1T34GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1 $\times$ 0.5 mm	SOT891					
74AUP1T34GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115					
74AUP1T34GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 $\times$ 1.0 $\times$ 0.35 mm	SOT1202					
74AUP1T34GX	–40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm	SOT1226					

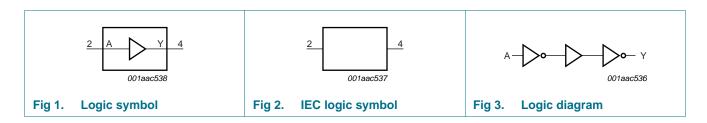
### 4. Marking

Table 2. Marking

Type number	Marking code <sup>[1]</sup>
74AUP1T34GW	pQ
74AUP1T34GM	pQ
74AUP1T34GF	pQ
74AUP1T34GN	pQ
74AUP1T34GS	pQ
74AUP1T34GX	pQ

<sup>[1]</sup> The pin 1 indicator is located on the lower left corner of the device, below the marking code.

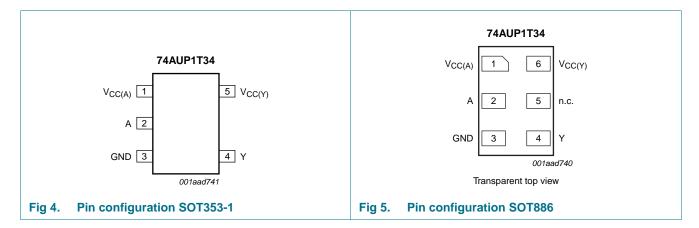
### 5. Functional diagram



Low-power dual supply translating buffer

### 6. Pinning information

#### 6.1 Pinning





### 6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	TSSOP5 and X2SON5 XSON6		
$V_{CC(A)}$	1	1	supply voltage port A
Α	2	2	data input A
GND	3	3	ground (0 V)
Υ	4	4	data output Y
n.c.	-	5	not connected
$V_{CC(Y)}$	5	6	supply voltage port Y

#### Low-power dual supply translating buffer

### 7. Functional description

Table 4. Function table[1]

Input	Output
A	Υ
L	L
Н	Н

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level.

### 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

		, , ,			•
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		-0.5	+4.6	V
$V_{CC(Y)}$	supply voltage Y		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-50	-	mA
VI	input voltage		[ <u>1</u> ] -0.5	+4.6	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	[ <u>1</u> ] -0.5	+4.6	V
I <sub>O</sub>	output current	$V_O = 0 V \text{ to } V_{CC(Y)}$	-	±20	mA
I <sub>CC</sub>	supply current		-	50	mA
$I_{GND}$	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$	[2] _	250	mW

<sup>[1]</sup> The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

<sup>[2]</sup> For TSSOP5 packages: above 87.5  $^{\circ}$ C the value of P<sub>tot</sub> derates linearly with 4.0 mW/K. For XSON6 and X2SON5 packages: above 118  $^{\circ}$ C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

### Low-power dual supply translating buffer

### 9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		1.1	3.6	V
$V_{CC(Y)}$	supply voltage Y		1.1	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage		0	$V_{CC(Y)}$	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	control and data inputs; V <sub>CC(A)</sub> = 1.1 V to 3.6 V	0	200	ns/V

### 10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = 2	5 °C					
$V_{IH}$	HIGH-level	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V; } V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	$0.65 \times V_{CC(A)}$	-	-	V
ir	input voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	1.6	-	-	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V <sub>IL</sub>	LOW-level input	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	$0.35 \times V_{CC(A)}$	V
	voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.7	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$				
	output voltage	$I_{O} = -20 \mu A$ ; $V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	V <sub>CC(Y)</sub> - 0.1	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	$0.75 \times V_{CC(Y)}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.6	-	-	V
$V_{OL}$	LOW-level	$V_I = V_{IL}$				
	output voltage	$I_O = 20 \mu A$ ; $V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		$I_O = 1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC(Y)}$	V
		$I_O = 1.7 \text{ mA}$ ; $V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	-	-	0.31	V
		$I_O = 1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	-	-	0.31	V
		$I_O = 2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.31	V
		$I_O = 3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.44	V
		$I_O = 2.7 \text{ mA}$ ; $V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$		-	0.31	V
		$I_O = 4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.44	V
lı	input leakage current	$V_I = 0 \text{ V to } 3.6 \text{ V}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	±0.1	μΑ

**Table 7. Static characteristics** ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Parameter	Conditions	Min	Тур	Max	Unit
power-off leakage current	A input; $V_I = 0 \text{ V to } 3.6 \text{ V}$ ; $V_{CC(A)} = 0 \text{ V}$ ; $V_{CC(Y)} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.2	μΑ
	Y output; $V_O = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V to 3.6 V; $V_I = 0$ V or 3.6 V; $V_{CC(Y)} = 0$ V	-	-	±0.2	μА
additional power-off	A input; $V_1 = 0 \text{ V to } 3.6 \text{ V}$ ; $V_{CC(A)} = 0 \text{ V to } 0.2 \text{ V}$ ; $V_{CC(Y)} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.2	μА
leakage current	Y output; $V_O = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V to 3.6 V; $V_I = 0$ V or 3.6 V; $V_{CC(Y)} = 0$ V to 0.2 V	-	-	±0.2	μΑ
supply current	port A; $V_I = GND$ or $V_{CC(A)}$ ; $I_O = 0$ A				
	$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
	$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	-	0.5	μΑ
	$V_{CC(A)} = 0 \text{ V}; V_{CC(Y)} = 3.6 \text{ V}$	-	0.0	-	μΑ
	port Y; $V_I = GND$ or $V_{CC(A)}$ ; $I_O = 0$ A				
	$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
	$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	0.0	-	μΑ
	$V_{CC(A)} = 0 \text{ V}; V_{CC(Y)} = 3.6 \text{ V}$	-	-	0.5	μΑ
	port A and port Y; $V_I$ = GND or $V_{CC(A)}$ ; $I_O$ = 0 A; $V_{CC(A)}$ = $V_{CC(Y)}$ = 1.1 V to 3.6 V	-	-	0.5	μΑ
additional supply current	A input; $V_{CC(A)} = 3.3 \text{ V}$ ; $V_{CC(Y)} = 0 \text{ V}$ to 3.6 V; $V_I = V_{CC(A)} - 0.6 \text{ V}$	-	-	40	μΑ
input capacitance	A input; $V_{CC(A)} = V_{CC(Y)} = 0 \text{ V to } 3.6 \text{ V};$ $V_I = \text{GND or } V_{CC(A)}$	-	1.0	-	pF
output capacitance	Y output; $V_O = GND$ ; $V_{CC(Y)} = 0 V$ ; $V_{CC(A)} = 0 V$ to 3.6 V	-	1.8	-	pF
40 °C to +85 °C					
HIGH-level	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	$0.65 \times V_{CC(A)}$	-	-	V
input voltage	$V_{CC(A)}$ = 2.3 V to 2.7 V; $V_{CC(Y)}$ = 1.1 V to 3.6 V	1.6	-	-	V
	$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
LOW-level input	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	$0.35 \times V_{CC(A)}$	V
voltage	$V_{CC(A)}$ = 2.3 V to 2.7 V; $V_{CC(Y)}$ = 1.1 V to 3.6 V	-	-	0.7	V
	$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V
HIGH-level	$V_{I} = V_{IH}$				
output voltage	$I_O = -20~\mu\text{A};~V_{CC(A)} = V_{CC(Y)} = 1.1~V$ to 3.6 $V$	$V_{CC(Y)} - 0.1$	-	-	V
	$I_{O} = -1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	$0.7 \times V_{CC(Y)}$	-	-	V
	$I_O = -1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	1.03	-	-	V
	$I_O = -1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	1.30	-	-	V
	$I_O = -2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.97	-	-	V
	$I_O = -3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.85	-	-	V
	$I_O = -2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.67	-	-	V
	$I_{O} = -4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.55	-	-	V
	additional power-off leakage current additional power-off leakage current supply current supply current input capacitance output capacitance 40 °C to +85 °C HIGH-level input voltage	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{c} \text{power-off} \\ \text{leakage current} \\ \text{leakage current} \\ \text{Vac(} (a) = 0 \ V; \ Vac() = 0 \ V \ to 3.6 \ V; \ Vac() = 0 \ V \ Vac() = 0 \ V; \ Vac() = 0 \ Vac() = 0 \$

**Table 7. Static characteristics** ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>OL</sub> LOW-level output voltage		$V_I = V_{IL}$				
VOL	output voltage	$I_O = 20 \mu A$ ; $V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		$I_O = 1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC(Y)}$	V
		$I_O = 1.7 \text{ mA}$ ; $V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	-	-	0.37	V
		$I_{O} = 1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	-	-	0.35	V
		$I_O = 2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.33	V
		$I_O = 3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.45	V
		$I_{O} = 2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.33	V
		$I_{O} = 4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.45	V
l <sub>l</sub>	input leakage current	$V_I = 0 \text{ V to } 3.6 \text{ V}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	±0.5	μΑ
OFF	power-off leakage current	A input; $V_I = 0 \text{ V to } 3.6 \text{ V}$ ; $V_{CC(A)} = 0 \text{ V}$ ; $V_{CC(Y)} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.5	μΑ
		Y output; $V_O = 0 \text{ V to } 3.6 \text{ V}; V_{CC(A)} = 0 \text{ V to } 3.6 \text{ V}; V_I = 0 \text{ V or } 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	-	±0.5	μΑ
Δl <sub>OFF</sub>	additional power-off leakage current	A input; $V_I = 0 \text{ V to } 3.6 \text{ V}$ ; $V_{CC(A)} = 0 \text{ V to } 0.2 \text{ V}$ ; $V_{CC(Y)} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.6	μΑ
		Y output; $V_O = 0 \text{ V to } 3.6 \text{ V}; V_{CC(A)} = 0 \text{ V to } 3.6 \text{ V}; V_I = 0 \text{ V or } 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μΑ
lcc	supply current	port A; $V_I = GND$ or $V_{CC(A)}$ ; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	-	0.9	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(Y)} = 3.6 \text{ V}$	-	0.0	-	μΑ
		port Y; $V_I = GND$ or $V_{CC(A)}$ ; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	0.0	-	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(Y)} = 3.6 \text{ V}$	-	-	0.9	μΑ
		port A and port Y; $V_I$ = GND or $V_{CC(A)}$ ; $I_O$ = 0 A; $V_{CC(A)}$ = $V_{CC(Y)}$ = 1.1 V to 3.6 V	-	-	0.9	μΑ
∆I <sub>CC</sub>	additional supply current	A input; $V_{CC(A)} = 3.3 \text{ V}$ ; $V_{CC(Y)} = 0 \text{ V}$ to 3.6 V; $V_{I} = V_{CC(A)} - 0.6 \text{ V}$	-	-	50	μΑ
T <sub>amb</sub> = -	40 °C to +125 °C					
ViH	HIGH-level	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	$0.7 \times V_{CC(A)}$	-	-	V
	input voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V; } V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	1.6	-	-	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V <sub>IL</sub>	LOW-level input	$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	$0.3 \times V_{\text{CC(A)}}$	V
	voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.7	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}; V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V

**Table 7. Static characteristics** ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$				
011	output voltage	$I_{O} = -20 \mu A$ ; $V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	$V_{CC(Y)} - 0.11$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	$0.6 \times V_{CC(Y)}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.77	-	-	V
		$I_O = -3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	2.30	-	-	V
V <sub>OL</sub>	LOW-level	$V_I = V_{IL}$				
	output voltage	$I_O = 20 \mu A$ ; $V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	0.11	V
		$I_{O} = 1.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC(Y)}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.4 \text{ V}$	-	-	0.41	V
		$I_0 = 1.9 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 1.65 \text{ V}$	-	-	0.39	V
		$I_{O} = 2.3 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.36	V
		$I_0 = 3.1 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 2.3 \text{ V}$	-	-	0.50	V
		$I_0 = 2.7 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.36	V
		$I_0 = 4.0 \text{ mA}; V_{CC(A)} = V_{CC(Y)} = 3.0 \text{ V}$	-	-	0.50	V
I <sub>I</sub>	input leakage current	$V_I = 0 \text{ V to } 3.6 \text{ V}; V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μΑ
I <sub>OFF</sub>	power-off leakage current	A input; $V_I = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC(A)} = 0 \text{ V}; V_{CC(Y)} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μΑ
	3	Y output; $V_O = 0 \text{ V to } 3.6 \text{ V}; V_{CC(A)} = 0 \text{ V to } 3.6 \text{ V}; V_I = 0 \text{ V or } 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	-	±0.75	μΑ
Δl <sub>OFF</sub>	additional power-off	A input; $V_I = 0 \text{ V to } 3.6 \text{ V}$ ; $V_{CC(A)} = 0 \text{ V to } 0.2 \text{ V}$ ; $V_{CC(Y)} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μΑ
	leakage current	Y output; $V_O = 0 \text{ V to } 3.6 \text{ V}; V_{CC(A)} = 0 \text{ V to } 3.6 \text{ V}; V_I = 0 \text{ V or } 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.75	μΑ
lcc	supply current	port A; $V_I = GND$ or $V_{CC(A)}$ ; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	-	1.4	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(Y)} = 3.6 \text{ V}$	-	0.0	-	μΑ
		port Y; $V_I = GND$ or $V_{CC(A)}$ ; $I_O = 0$ A				
		$V_{CC(A)} = V_{CC(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(Y)} = 0 \text{ V}$	-	0.0	-	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(Y)} = 3.6 \text{ V}$	-	-	1.4	μΑ
		port A and port Y; $V_I = \text{GND or } V_{\text{CC}(A)}; I_O = 0 \text{ A};$ $V_{\text{CC}(A)} = V_{\text{CC}(Y)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
Δl <sub>CC</sub>	additional supply current	A input; $V_{CC(A)} = 3.3 \text{ V}$ ; $V_{CC(Y)} = 0 \text{ V}$ to 3.6 V; $V_{I} = V_{CC(A)} - 0.6 \text{ V}$	-	-	75	μΑ

### Low-power dual supply translating buffer

### 11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions			25 °C		-40			Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 5 pl	F; V <sub>CC(A)</sub> = 1.1 V to	1.3 V				•		'		
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	[2]							
		V <sub>CC(Y)</sub> = 1.1 V to 1.3 V		2.6	9.8	25.4	2.3	25.9	25.9	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.4	7.1	15.3	2.2	16.3	16.7	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.1	6.0	12.7	1.9	13.8	14.3	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.0	5.1	9.8	2.0	10.5	10.9	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.1	4.7	8.8	1.9	9.1	9.3	ns
C <sub>L</sub> = 5 pl	F; $V_{CC(A)} = 1.4 \text{ V to}$	1.6 V								
$t_{pd}$	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.3	9.1	23.9	2.0	24.5	24.5	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.1	6.4	13.6	1.9	14.7	15.2	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		1.8	5.3	10.9	1.6	12.1	12.6	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.7	4.3	7.8	1.6	8.7	9.2	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		1.8	3.9	6.6	1.6	7.1	7.5	ns
C <sub>L</sub> = 5 pl	F; $V_{CC(A)} = 1.65 \text{ V to}$	1.95 V								
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.2	8.8	23.2	1.9	23.9	24.0	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.0	6.0	13.0	1.8	14.1	14.6	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		1.8	4.9	10.3	1.5	11.4	12.0	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.6	3.9	7.2	1.5	8.0	8.5	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		1.7	3.5	5.9	1.5	6.4	6.8	ns
C <sub>L</sub> = 5 pl	F; $V_{CC(A)} = 2.3 \text{ V to}$	2.7 V								
$t_{pd}$	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.2	8.4	22.8	1.9	23.4	23.4	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		1.9	5.7	12.3	1.8	13.4	14.0	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		1.7	4.6	9.6	1.5	10.7	11.2	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.5	3.5	6.3	1.5	7.2	7.7	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		1.6	3.1	5.1	1.4	5.6	6.0	ns
$C_L = 5 pl$	F; $V_{CC(A)} = 3.0 \text{ V to}$	3.6 V								
$t_{pd}$	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.2	8.1	22.5	1.9	22.9	22.9	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		1.9	5.4	12.0	1.8	12.9	13.4	ns
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		1.7	4.3	9.2	1.5	10.2	10.7	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.5	3.3	6.0	1.5	6.7	7.2	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		1.6	2.9	4.8	1.4	5.2	5.5	ns

**Table 8. Dynamic characteristics** ...continued Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 9</u>.

Symbol	Parameter	Conditions			25 °C		-40			Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 10	pF; V <sub>CC(A)</sub> = 1.1 V to	1.3 V						'		
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	[2]							
		V <sub>CC(Y)</sub> = 1.1 V to 1.3 V		2.6	10.7	27.1	2.5	27.6	27.6	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.6	7.7	16.7	2.3	17.5	17.6	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.7	6.6	13.4	2.4	14.2	14.7	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.2	5.6	10.3	2.2	11.0	11.4	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.5	5.3	9.5	2.2	9.7	10.0	ns
C <sub>L</sub> = 10	pF; $V_{CC(A)} = 1.4 \text{ V to}$	1.6 V								
$t_{pd}$	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.4	10.0	25.6	2.2	26.1	26.1	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.4	7.0	15.0	2.0	15.8	16.4	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.4	5.9	11.6	2.1	12.5	13.1	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.0	4.8	8.4	1.9	9.2	9.7	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.2	4.4	7.4	1.9	7.7	8.1	ns
C <sub>L</sub> = 10	$pF; V_{CC(A)} = 1.65 V t$	to 1.95 V								
$t_{pd}$	propagation delay	A to Y; see Figure 8								
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.3	9.7	24.8	2.1	25.5	25.7	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.3	6.6	14.3	2.0	15.3	15.8	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.3	5.5	11.0	2.0	11.9	12.5	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.9	4.4	7.7	1.8	8.6	9.0	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.1	4.0	6.6	1.8	7.1	7.4	ns
C <sub>L</sub> = 10	pF; $V_{CC(A)} = 2.3 \text{ V to}$	2.7 V								
$t_{pd}$	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.3	9.3	24.4	2.1	25.1	25.1	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.2	6.3	13.6	1.9	14.6	15.1	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.2	5.1	10.3	2.0	11.2	11.7	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.8	4.1	6.9	1.8	7.7	8.2	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.0	3.6	5.8	1.7	6.3	6.6	ns
C <sub>L</sub> = 10	pF; $V_{CC(A)} = 3.0 \text{ V to}$									
$t_{pd}$	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		2.3	9.0	24.2	2.1	24.6	24.6	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		2.2	6.0	13.3	1.9	14.1	14.6	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.2	4.9	9.9	2.0	10.6	11.2	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		1.8	3.9	6.5	1.8	7.3	7.7	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.0	3.5	5.4	1.7	5.8	6.2	ns

**Table 8. Dynamic characteristics** ...continued Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 9</u>.

Symbol	Parameter	Conditions			25 °C		-40	0 °C to +1	125 °C	Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 15	pF; V <sub>CC(A)</sub> = 1.1 V to	1.3 V			'			'		
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		3.0	11.5	28.6	2.8	29.2	29.2	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		3.1	8.3	17.3	2.7	18.6	19.1	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.8	7.1	14.1	2.7	15.2	15.8	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.6	6.1	11.1	2.7	11.6	12.1	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.9	5.7	9.9	2.6	10.3	10.6	ns
C <sub>L</sub> = 15	pF; V <sub>CC(A)</sub> = 1.4 V to	1.6 V								
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	2]							
		V <sub>CC(Y)</sub> = 1.1 V to 1.3 V		2.8	10.8	27.1	2.6	27.7	27.7	ns
		V <sub>CC(Y)</sub> = 1.4 V to 1.6 V		2.8	7.6	15.7	2.4	17.0	17.6	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		2.5	6.3	12.3	2.4	13.5	14.1	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.3	5.3	9.2	2.4	9.9	10.3	ns
		V <sub>CC(Y)</sub> = 3.0 V to 3.6 V		2.6	4.9	7.8	2.3	8.3	8.7	ns
C <sub>L</sub> = 15	pF; V <sub>CC(A)</sub> = 1.65 V t	to 1.95 V								
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	2]							
		V <sub>CC(Y)</sub> = 1.1 V to 1.3 V		2.7	10.5	26.4	2.5	27.1	27.3	ns
		V <sub>CC(Y)</sub> = 1.4 V to 1.6 V		2.7	7.2	15.0	2.3	16.4	17.0	ns
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		2.4	6.0	11.7	2.3	12.8	13.5	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.2	4.9	8.5	2.2	9.2	9.7	ns
		V <sub>CC(Y)</sub> = 3.0 V to 3.6 V		2.5	4.5	7.1	2.2	7.7	8.0	ns
C <sub>L</sub> = 15	pF; V <sub>CC(A)</sub> = 2.3 V to	2.7 V								
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	2]							
		V <sub>CC(Y)</sub> = 1.1 V to 1.3 V		2.6	10.1	26.0	2.4	26.7	26.7	ns
		V <sub>CC(Y)</sub> = 1.4 V to 1.6 V		2.7	6.9	14.3	2.3	15.7	16.3	ns
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		2.4	5.6	10.9	2.2	12.1	12.7	ns
		V <sub>CC(Y)</sub> = 2.3 V to 2.7 V		2.1	4.5	7.6	2.2	8.4	8.9	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.4	4.1	6.2	2.1	6.8	7.2	ns
C <sub>L</sub> = 15	pF; $V_{CC(A)} = 3.0 \text{ V to}$	3.6 V								
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	2]							
		V <sub>CC(Y)</sub> = 1.1 V to 1.3 V		2.6	9.8	25.7	2.4	26.2	26.2	ns
		V <sub>CC(Y)</sub> = 1.4 V to 1.6 V		2.7	6.6	14.0	2.3	15.2	15.7	ns
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		2.4	5.4	10.5	2.2	11.6	12.1	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.1	4.3	7.3	2.2	7.9	8.4	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		2.4	3.9	5.9	2.1	6.4	6.8	ns

**Table 8. Dynamic characteristics** ...continued Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 9</u>.

Symbol	Parameter	Conditions			25 °C		-40 °C to +125 °C			Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 30	oF; V <sub>CC(A)</sub> = 1.1 V to	1.3 V						'		
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		3.7	13.7	32.9	3.5	33.5	33.5	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		3.6	9.8	19.5	3.6	20.9	21.4	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		3.7	8.4	15.9	3.5	17.0	17.7	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		3.0	7.2	12.2	3.4	12.7	13.2	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.8	6.8	10.9	3.4	12.2	12.5	ns
C <sub>L</sub> = 30	oF; $V_{CC(A)} = 1.4 \text{ V to}$	1.6 V								
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		3.5	13.1	31.5	3.2	32.0	32.0	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		3.3	9.1	17.8	3.3	19.2	19.9	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		3.4	7.6	14.2	3.2	15.4	16.0	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.8	6.4	10.3	3.1	11.0	11.5	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.5	5.9	8.9	3.1	10.1	10.5	ns
C <sub>L</sub> = 30	oF; V <sub>CC(A)</sub> = 1.65 V t	o 1.95 V								
t <sub>pd</sub>	<sub>d</sub> propagation delay	A to Y; see Figure 8	2]							
		V <sub>CC(Y)</sub> = 1.1 V to 1.3 V		3.4	12.7	30.7	3.1	31.5	31.5	ns
		V <sub>CC(Y)</sub> = 1.4 V to 1.6 V		3.2	8.8	17.2	3.2	18.7	19.3	ns
		V <sub>CC(Y)</sub> = 1.65 V to 1.95 V		3.3	7.3	13.5	3.1	14.7	15.4	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.7	6.0	9.6	3.0	10.4	10.9	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.4	5.6	8.2	2.9	9.4	9.8	ns
C <sub>L</sub> = 30	oF; $V_{CC(A)} = 2.3 \text{ V to}$	2.7 V								
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	2]							
		V <sub>CC(Y)</sub> = 1.1 V to 1.3 V		3.3	12.4	30.3	3.1	31.0	31.0	ns
		V <sub>CC(Y)</sub> = 1.4 V to 1.6 V		3.2	8.4	16.5	3.1	18.0	18.7	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		3.2	6.9	12.8	3.0	14.0	14.6	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.6	5.6	8.8	2.9	9.6	10.1	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.3	5.2	7.3	2.9	8.5	9.0	ns
C <sub>L</sub> = 30	oF; $V_{CC(A)} = 3.0 \text{ V to}$	3.6 V								
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC(Y)} = 1.1 \text{ V to } 1.3 \text{ V}$		3.3	12.0	30.0	3.1	30.5	30.5	ns
		$V_{CC(Y)} = 1.4 \text{ V to } 1.6 \text{ V}$		3.2	8.1	16.2	3.1	17.5	18.1	ns
		$V_{CC(Y)} = 1.65 \text{ V to } 1.95 \text{ V}$		3.2	6.7	12.4	3.0	13.4	14.1	ns
		$V_{CC(Y)} = 2.3 \text{ V to } 2.7 \text{ V}$		2.6	5.5	8.5	2.9	9.1	9.6	ns
		$V_{CC(Y)} = 3.0 \text{ V to } 3.6 \text{ V}$		3.2	5.0	7.0	2.9	8.1	8.5	ns

#### Low-power dual supply translating buffer

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions			25 °C		-40 °C to +125 °C			Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5 pl$	F, 10 pF, 15 pF and	30 pF			•		•			
C <sub>PD</sub> power diss	power dissipation	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC(A)}$	[3][4]							
	capacitance	$V_{CC(A)} = V_{CC(Y)} = 1.2 \text{ V}$		-	3.8	-	-	-	-	pF
		$V_{CC(A)} = V_{CC(Y)} = 1.5 \text{ V}$		-	3.8	-	-	-	-	pF
		$V_{CC(A)} = V_{CC(Y)} = 1.8 \text{ V}$		-	4.1	-	-	-	-	pF
		$V_{CC(A)} = V_{CC(Y)} = 2.5 \text{ V}$		-	4.2	-	-	-	-	pF
		$V_{CC(A)} = V_{CC(Y)} = 3.3 \text{ V}$		-	4.6	-	-	-	-	pF

- [1] All typical values are measured at nominal  $V_{CC}$ .
- [2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .
- [3] All specified values are the average typical values over all stated loads.
- [4]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

$$P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}{}^2 \times f_o) \text{ where:}$$

 $f_i$  = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

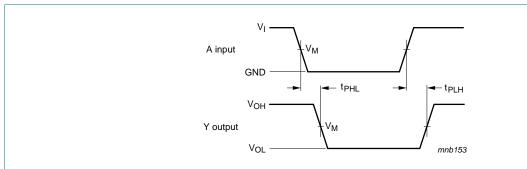
C<sub>I</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

#### 12. Waveforms



Measurement points are given in Table 9.

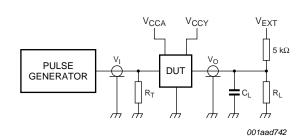
Logic levels:  $V_{OL}$  and  $V_{OH}$  are typical output voltage drop that occur with the output load.

Fig 8. The data input (A) to output (Y) propagation delays

Table 9. Measurement points

Supply voltage	Output	Input		
$V_{CC(A)}/V_{CC(Y)}$	V <sub>M</sub>	V <sub>M</sub>	VI	$t_r = t_f$
1.1 V to 3.6 V	$0.5 \times V_{CC(Y)}$	$0.5 \times V_{\text{CC(A)}}$	V <sub>CC(A)</sub>	≤ 3.0 ns

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Test data is given in Table 10.

Definitions for test circuit:

R<sub>L</sub> = Load resistance.

C<sub>L</sub> = Load capacitance including jig and probe capacitance.

 $R_T$  = Termination resistance should be equal to the output impedance  $Z_0$  of the pulse generator.

 $V_{\text{EXT}}$  = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

#### Table 10. Test data

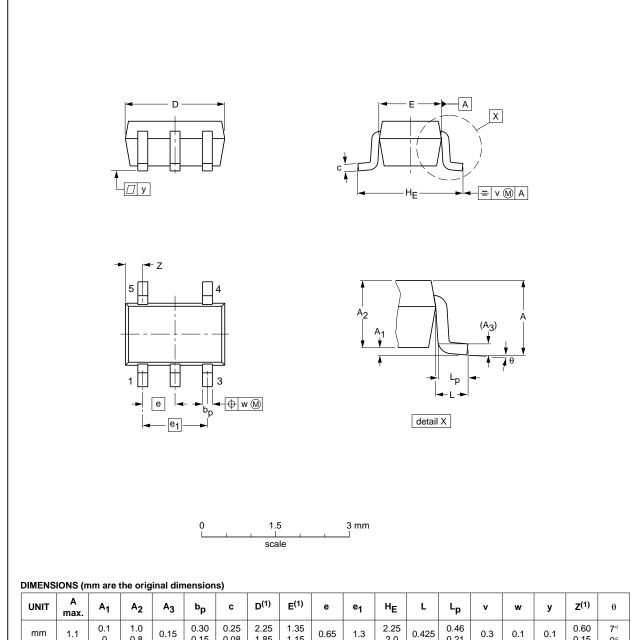
Supply voltage	Load		V <sub>EXT</sub>
$V_{CC(A)}/V_{CC(Y)}$	C <sub>L</sub>	R <sub>L</sub> [1]	t <sub>PLH</sub> , t <sub>PHL</sub>
1.1 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	$5$ k $\Omega$ or $1$ M $\Omega$	open

[1] For measuring enable and disable times  $R_L = 5 \text{ k}\Omega$ , for measuring propagation delays, setup and hold times and pulse width  $R_L = 1 \text{ M}\Omega$ .

### 13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	e <sub>1</sub>	HE	L	Lp	v	w	у	Z <sup>(1)</sup>	θ
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

IE REFERENCES				EUROPEAN	ISSUE DATE
IEC	JEDEC JEITA		PROJECTION	1330E DATE	
	MO-203	SC-88A			<del>-00-09-01</del> 03-02-19
	IEC				IEC JEDEC JEITA PROJECTION

Fig 10. Package outline SOT353-1 (TSSOP5)

#### Low-power dual supply translating buffer

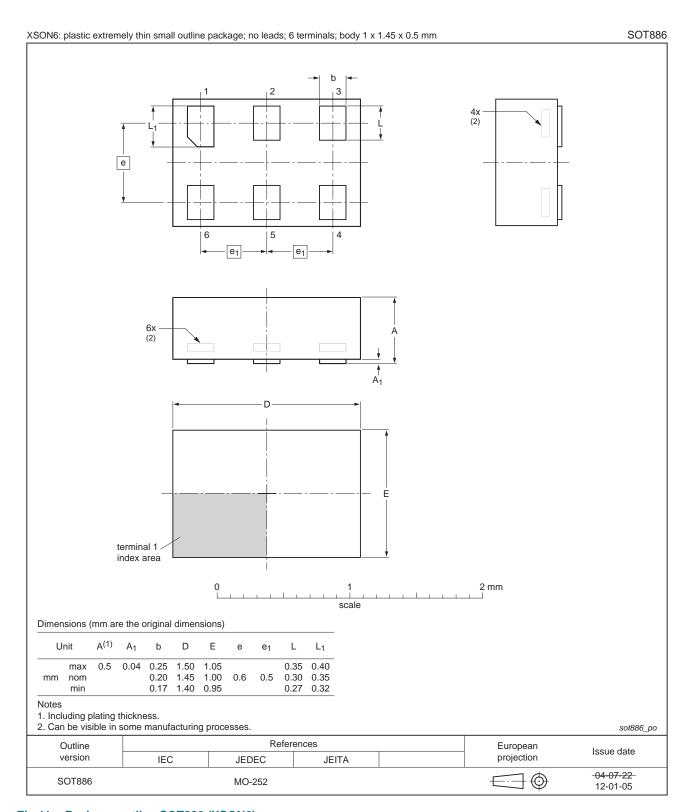


Fig 11. Package outline SOT886 (XSON6)

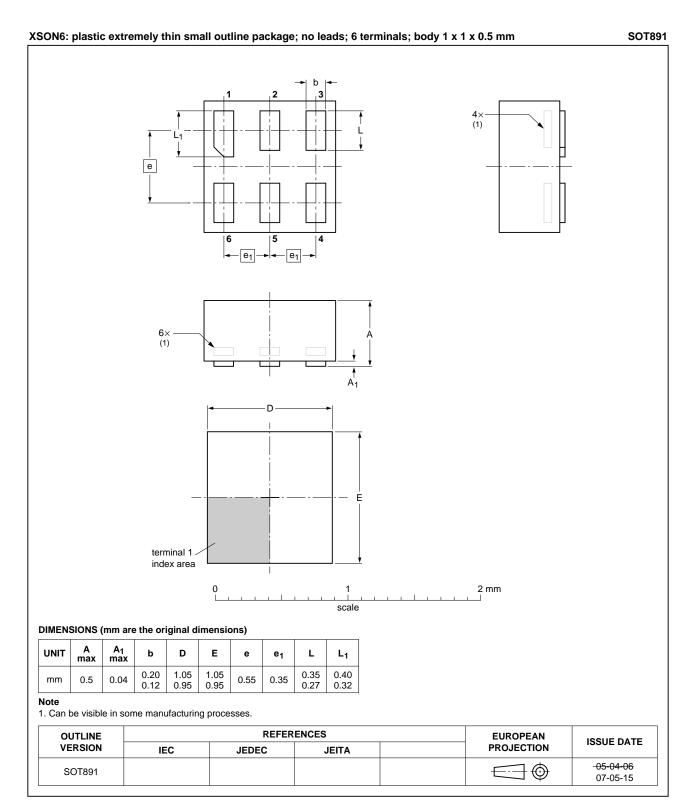


Fig 12. Package outline SOT891 (XSON6)

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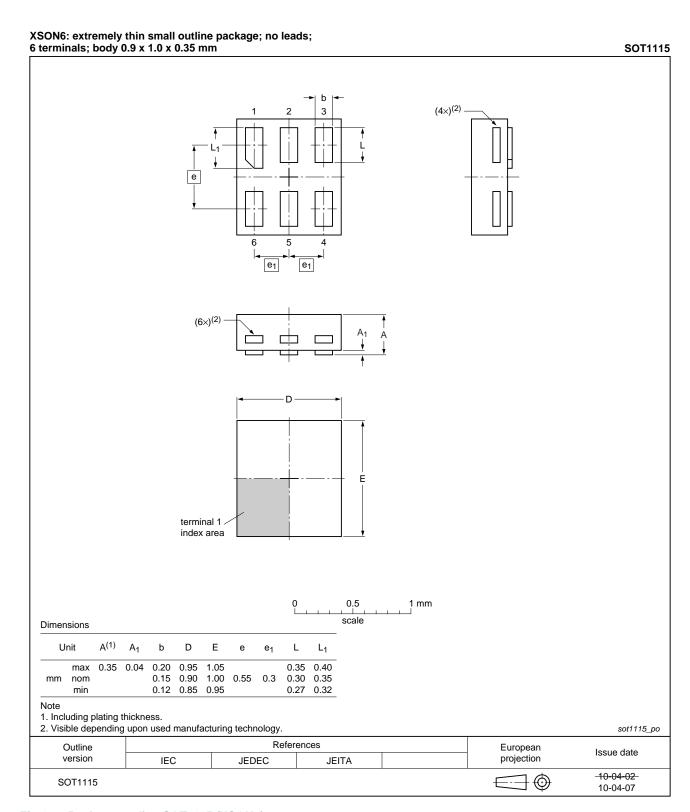


Fig 13. Package outline SOT1115 (XSON6)

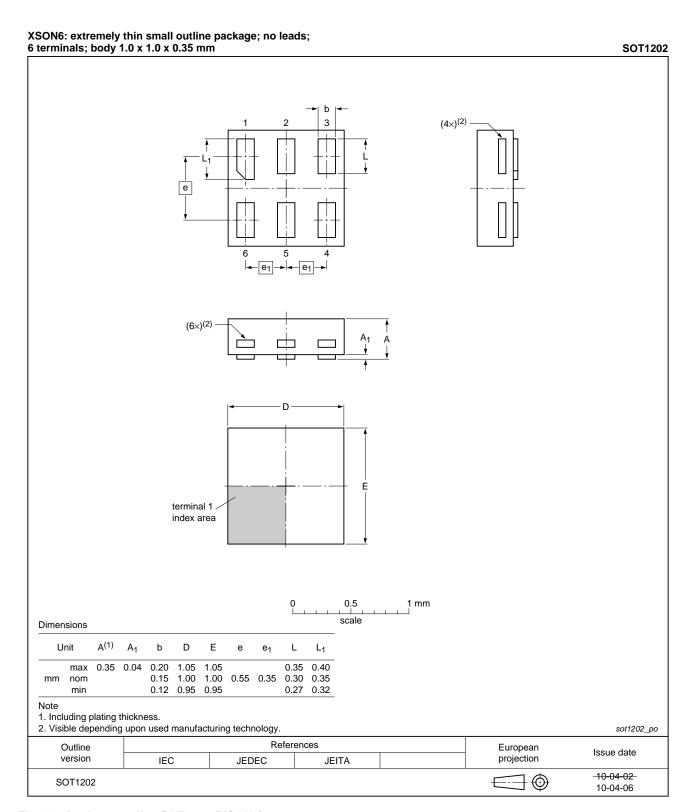


Fig 14. Package outline SOT1202 (XSON6)

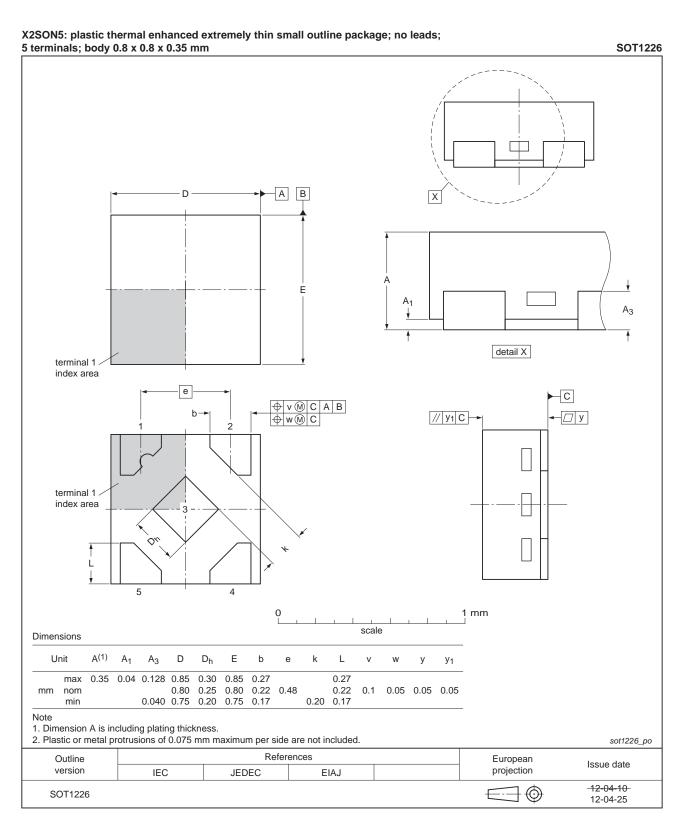


Fig 15. Package outline SOT1226 (X2SON5)

### Low-power dual supply translating buffer

### 14. Abbreviations

#### Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

### 15. Revision history

#### Table 12. Revision history

	•			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1T34 v.5	20130904	Product data sheet	-	74AUP1T34 v.4
Modifications:	<ul> <li>Added type</li> </ul>	number 74AUP1T34GX (S	OT1226)	
74AUP1T34 v.4	20120316	Product data sheet	-	74AUP1T34 v.3
Modifications:	<ul> <li>Package ou</li> </ul>	tline drawing of SOT886 (F	igure 11) modified.	
74AUP1T34 v.3	20111128	Product data sheet	-	74AUP1T34 v.2
Modifications:	<ul> <li>Legal pages</li> </ul>	s updated.		
74AUP1T34 v.2	20100819	Product data sheet	-	74AUP1T34 v.1
74AUP1T34 v.1	20061204	Product data sheet	-	-

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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- [2] The term 'short data sheet' is explained in section "Definitions"
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